

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	4741	dummy near2 pattern\$4	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
2	BRS	L2	69526	dummy	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
3	BRS	L3	1946	dummy near2 wir\$6	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
4	BRS	L4	448201	wiring patterns near4 (gate adj electrode)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
5	BRS	L5	3730	(wiring patterns near4 (gate adj electrode)) same dummy	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	867	((wiring patterns near4 (gate adj electrode)) same dummy) and @ad<"19930716"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
7	BRS	L7	219	(signal near2 wiring) and (power adj source adj wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
8	BRS	L8	56178	wiring near4 pattern\$6	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
9	BRS	L9	70106	dummy	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
10	BRS	L10	70106	dummy or dummies	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	1288	(dummy or dummies) near2 wiring	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
12	BRS	L12	627	(wiring near4 pattern\$6) and ((dummy or dummies) near2 wiring)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
13	BRS	L13	2221	(wiring near4 pattern\$6) same level	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
14	BRS	L14	1069	(first adj wiring) same (second adj wiring) same (third adj wiring)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
15	BRS	L15	164972 1	simultaneous\$6 or concuren\$6 or "at the same time"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	IS&R	L16	366	(257/374).CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
17	BRS	L17	61	((257/374).CCLS.) and (pn adj junction)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
18	BRS	L18	34	((257/374).CCLS.) and (pn adj junction)) and polycrystal\$6	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
19	BRS	L19	207	separation near4 (polycrystal\$6 or poly- crystal\$6)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
20	BRS	L20	14	(separation near4 (polycrystal\$6 or poly- crystal\$6)) and (SOI or "silicon on insulat\$6")	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
21	BRS	L21	34327	(dummy or interpolcation or interpolate or auxiliary) near2 (electrode or wire or wiring or line)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
22	BRS	L22	3953	source adj wiring	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
23	BRS	L23	112	((dummy or interpolcation or interpolate or auxiliary) near2 (electrode or wire or wiring or line)) and (gate adj wiring) and (source adj wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
24	BRS	L24	5013	gate adj wiring	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
25	BRS	L25	6271	((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
26	BRS	L26	6177	signal adj wiring	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
27	BRS	L49	764	dummy adj wiring	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
28	BRS	L51	214497 7	(dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39
29	BRS	L52	63137	((dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
30	BRS	L53	47665	wiring near2 pattern\$6	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
31	BRS	L54	735808 3	connect\$6 or link\$6	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
32	BRS	L55	36	(wiring near2 pattern\$6) near4 (connect\$6 or link\$6) near4 (((dummy or dummies or interpolation or inter- polation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode))	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
33	BRS	L56	576415 4	wire or wiring or line or conductive or conductor or interconnect	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
34	BRS	L58	54032	(wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
35	BRS	L59	21164	((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716")	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
36	BRS	L60	6463	((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716")) and ((dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
37	IS&R	L62	947	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
38	IS&R	L63	771	(438/200) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
39	IS&R	L64	149	(438/737) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
40	IS&R	L65	129	(438/926) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
41	IS&R	L66	1030	(438/151) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
42	IS&R	L67	1106	(438/585).CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
43	BRS	L29	1	((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716") and (dummy near2 pattern\$4)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
44	BRS	L34	1	((wiring patterns near4 (gate adj electrode)) same dummy) and @ad<"19930716") and IGFET	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
45	BRS	L27	7	((first adj wiring) same (second adj wiring) same (third adj wiring)) and IGFET	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
46	BRS	L30	5	((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716") and dummy	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
47	BRS	L31	2	(dummy near2 wir\$6) and IGFET	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
48	BRS	L33	18	((dummy near2 wir\$6) and MOS) and @ad<"19930716"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
49	BRS	L35	79	((signal near2 wiring) and (power adj source adj wiring)) and @ad<"19930716"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
50	BRS	L36	23	((signal near2 wiring) and (power adj source adj wiring)) and dummy	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
51	BRS	L37	6	((signal near2 wiring) and (power adj source adj wiring)) and dummy) and @ad<"19930716"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
52	BRS	L38	41	((wiring near4 pattern\$6) same level) and ((dummy or dummies) near2 wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
53	BRS	L39	87	((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
54	BRS	L40	42	((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies)) and (gate adj electrode)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
55	BRS	L41	24	(((((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies)) and (gate adj electrode)) and (simultaneous\$6 or concuren\$6 or "at the same time"))	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
56	BRS	L42	12	((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) and (gate adj wiring) and (source adj wiring) and (signal adj wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
57	BRS	L43	20	((((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)) and (gate adj wiring) and (source adj wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
58	BRS	L44	6	(gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)) and (signal adj wiring)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
59	BRS	L45	8	((gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6))) and (@ad<"19930716")	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
60	BRS	L46	86	(gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6))	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
61	BRS	L47	4	("5483366" "5986723" "6078366" "6201584").PN.	USPAT	2004/11/19 16:39
62	BRS	L48	16	("4563367" "4564997" "5016564" "4960073" "5022977" "5259922" "5344536" "5156703" "5183777" "5444207" "5290382" "4298419" "5368685" "4971651" "5350710" "5378311").PN.	USPAT	2004/11/19 16:39
63	BRS	L50	24	(dummy adj wiring) near4 "gate electrode"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
64	BRS	L57	5	((wiring near2 pattern\$6) near4 (connect\$6 or link\$6) near4 (((dummy or dummies or interpolation or inter-polation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode))) and (@ad<"19930716")	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
65	BRS	L61	132	(((((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716")) and ((dummy or dummies or interpolation or inter- polation or inter-pole or intermediat\$6 or auxiliary or temporary)) and ((second! or another or addition\$6) adj wir\$6)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39
66	BRS	L28	219	((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716"	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

	Type	L #	Hits	Search Text	DBs	Time Stamp
67	BRS	L32	208	(dummy near2 wir\$6) and MOS	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/11/19 16:39

DERWENT-ACC-NO: 1992-160403

DERWENT-WEEK: 199907

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TITLE: Semiconductor memory device for mfg. computer
DRAM - comprises semiconductor substrate, memory cell
array region having memory cells with transistor and
capacitor, peripheral circuit etc.

----- KWIC -----

Basic Abstract Text - ABTX (1):

A semiconductor memory device is formed on a semiconductor substrate (1) and has at least one memory cell array region, in which a multiplicity of memory cells is formed, each of which has a transistor (20) and a capacitor (30). The device also has a peripheral circuit region, in which a multiplicity of transistors (21) is formed, for application in a peripheral circuit. The device also has (1) a pair of gate electrode layers (6a, 6b) which are parallel to each other, and at a predetermined distance apart in the memory cell array region, where each pair is part of a transistor (20); (2) a gate electrode layer (6b) and a dummy wiring layer (6d) which are parallel to each other and at a predetermined distance apart in the peripheral circuit region and are part of the transistor (21) for use in the peripheral circuit. The distance between the gate electrode layers (6a, 6b) formed in pairs in the memory cell array region is about the same as the distance between the gate electrode layer (6b) and the dummy wiring layer (6d) in the peripheral circuit region.

Basic Abstract Text - ABTX (2):

Fabricating device comprises (a) forming a conductive layer (6) on the

semiconductor substrate and forming a resist layer (40) on the conductive layer; (b) removing the resist (40), leaving a section of the latter on the conductive layer which is to be used to form the gate electrode layer (6b) and the dummy wiring layer; (c) structuring the conductive layer (6) by etching, using the remaining sections of resist as a mask, and removing the remaining resist sections.

Derwent Accession Number - NRAN (1):
1992-160403

Equivalent Abstract Text - ABEQ (2):

The memory device comprises a pair of parallel gate electrodes each pair constituting a transistor. A second gate electrode layer and a dummy wiring layer at a predetermined spacing constitute the second transistor for use in the peripheral circuit.

Equivalent Abstract Text - ABEQ (3):

The spacing between the paired gate electrode layers is approx. the same as the spacing between the dummy wiring layer and the second gate electrode layer.